

L Number	Hits	Search Text	DB	Time stamp
-	0	("ferroelectric adj memory").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:31
-	0	("insulat\$ and substrate and contact adj hole and (burry buried)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:33
-	3514	ferroelectric adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:34
-	0	insulat\$3 and substrate and contact adj hole and (burry and burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:24
-	0	insulat\$3 and substrate and (burry and burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	337972	insulat\$3 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	1091	(ferroelectric adj memory) and (insulat\$3 and substrate )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	923	((ferroelectric adj memory) and (insulat\$3 and substrate )) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:37
-	330	((((ferroelectric adj memory) and (insulat\$3 and substrate )) and capacitor) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:37
-	3	(((((ferroelectric adj memory) and (insulat\$3 and substrate )) and capacitor) and contact adj hole) and blocking adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:13
-	12043	kwon.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:53
-	12043	kwon-s.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:53
-	134	kwon-s-y.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:54
-	134	'kwon, s y'.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:22

-	2	6162649.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:23
-	2	6379977.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:23
-	2	6210979.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:24
-	43	insulat\$3 and substrate and contact adj hole and (burry or burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:24
-	0	((438/3,253,254,238,396).CCLS.) and (insulat\$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:25
-	1	((257/295,298,310,532).CCLS.) and (insulat\$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:25
-	27	(((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole) and ((silicon adj oxynitride) or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:31
-	45	(((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:40
-	54	((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 17:02
-	124	((257/295,298,310,532).CCLS.) and buried near3 contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:41
-	2641	(257/295,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:43
-	4442	(257/295,296,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 16:05
-	5525	(438/3,253,254,238,396).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:46
-	2	5411911.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 16:05

-	29	((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/08 17:03
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